

**ULTRA-SMALL BUILT-IN DELAY
HIGH-PRECISION VOLTAGE DETECTOR**

CE8801 Series

■ Introduction

The CE8801 Series is a series of high-precision voltage detectors developed using CMOS process. The detection voltage is fixed internally, with an accuracy of $\pm 2.0\%$. Internal oscillator and counter timer can delay the release signal without external parts, delay time is 200 ms ($V_{DS}=V_{SS}$). Two output forms, Nch open-drain and CMOS output, are available.

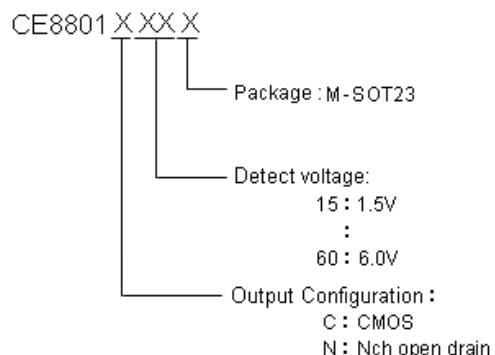
■ Features

- Ultra-low current consumption: $1.0\mu A@3.5V$ (Typ.)
- High-precision detection voltage: $\pm 2.0\%$
- Hysteresis characteristics: $-V_{DET} \times 5\%$ (Typ.)
- Operating voltage range: 0.95 V to 8.0 V
- Detection voltage: 1.5V to 6.0 V (0.1 V step)
- CE switching function of delay time (DS pin)
- Delay times: 200ms ($V_{DS}=V_{SS}$) (Typ.)
200us ($V_{DS}=V_{DD}$) (Typ.)
- Output forms:
 - NMOS open-drain output (Active Low)
 - CMOS output (Active Low)

■ Application

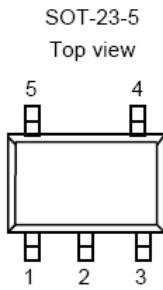
- Power monitor for portable equipment such as notebook computers, digital still cameras, PDA, and cellular phones.
- Constant voltage power monitors for cameras, video equipment and communication devices.
- Power monitor for microcomputers and reset for CPUs.

■ Ordering Information



■ Pin Configurations

Table 1 CE8801 Series (SOT-23-5)



PIN NO.	PIN name	Functions
1	DS	DS switch for delay time: “L”: 200ms delay; “H”: 200us delay.
2	V _{SS}	GND pin
3	NC	No connection
4	V _{OUT}	Voltage detection output pin
5	V _{DD}	Voltage input pin

■ Absolute Maximum Ratings

(Ta=25°C unless otherwise specified)

Item	Symbol	Absolute maximum ratings	Unit
Power supply voltage	V _{DD}	V _{SS} -0.3 ~ V _{SS} +8	V
Output voltage	V _{OUT}	V _{SS} -0.3 ~ V _{SS} +8	V
Power dissipation	SOT-23-3	250	mW
	SOT-23-5	250	mW
Operating ambient temperature	To _{pr}	-40 ~ +85	°C
Storage temperature	T _{stg}	-40 ~ +125	°C

■ Electrical Characteristics

(Ta=25°C unless otherwise specified)

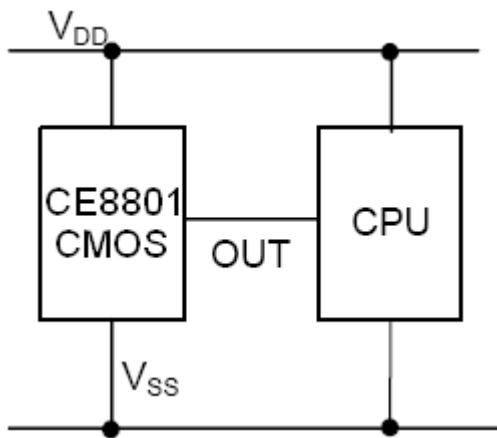
Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Detection voltage*1	-V _{DET}	—	-V _{DET(S)} ×0.98	-V _{DET(S)}	-V _{DET(S)} ×1.02	V	
Hysteresis width	V _{HYS}	—	0.02× -V _{DET(S)}	0.05× -V _{DET(S)}	0.08× -V _{DET(S)}	V	
Current consumption	I _{SS}	V _{DD} = -V _{DET} + 0.5V	CE8801X20~26	—	1.0	2.0	uA
			CE8801X26~39	—	1.2	2.5	uA
			CE8801X39~60	—	1.5	3.0	uA
Operating voltage	V _{DD}	—	0.95	—	8	V	
Output current	I _{OUT}	NMOS: V _{OUT} = 0.5 V V _{DD} = -V _{DET} - 0.5 V	CE8801X20~26	3.0	13.0	—	mA
			CE8801X26~39	3.0	15.0	—	mA
			CE8801X39~60	3.0	18.0	—	mA
		PMOS: V _{DD} - V _{OUT} = 0.5 V V _{DD} = -V _{DET} + 0.5 V	CE8801X20~26	1.5	4.0	—	mA
			CE8801X26~39	1.5	6.0	—	mA
			CE8801X39~60	1.5	8.0	—	mA

Leakage current	I_{LEAK}	Only for NMOS open-drain output products, $V_{DD} = 8.0 \text{ V}$, $V_{OUT} = 8.0 \text{ V}$		—	0.1	uA
temperature coefficient		Ta = -40°C ~ +85°C		±120		ppm/ °C
Delay time 1	t_{D1}	$V_{DD} = -V_{DET} + 1 \text{ V}$, DS PIN Low		200		ms
Delay time 2	t_{D2}	$V_{DD} = -V_{DET} + 1 \text{ V}$, DS PIN High		220		us
Input voltage	V_{SH}	DS PIN, $V_{DD} = 6.0 \text{ V}$	1.0	—	—	V
	V_{SH}	DS PIN, $V_{DD} = 6.0 \text{ V}$	—	—	0.3	V

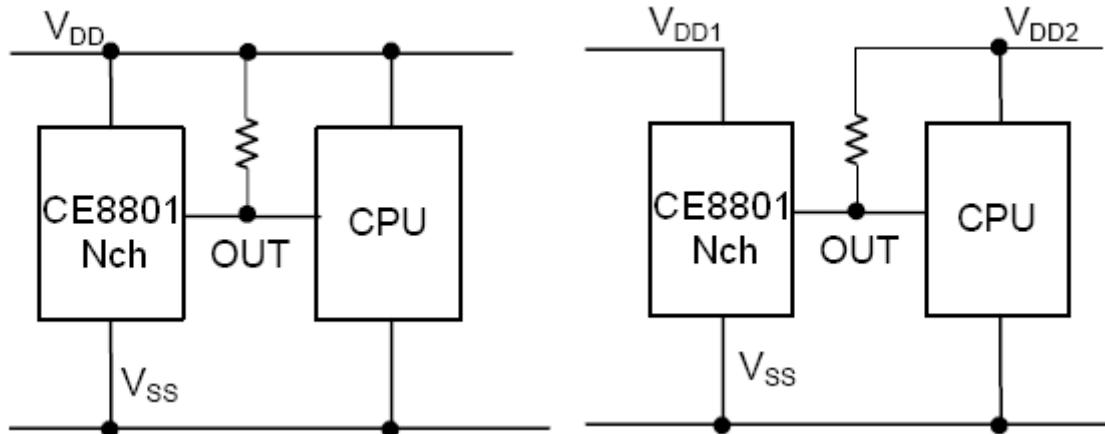
*1. $-V_{DET}$: Actual detection voltage value, $-V_{DET(S)}$: Specified detection voltage value

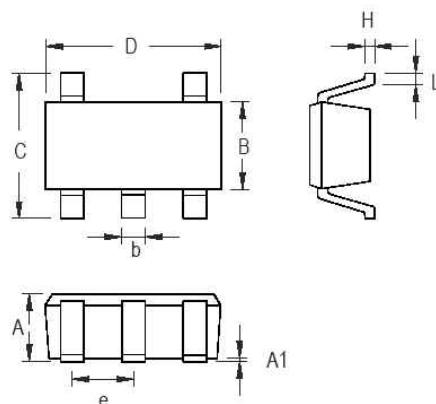
■ Application Circuit

1、CMOS output:



2、Nch open-drain



■ Package information**• SOT- 23- 5**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.889	1.295	0.035	0.051
A1	0.000	0.152	0.000	0.006
B	1.397	1.803	0.055	0.071
b	0.356	0.559	0.014	0.022
C	2.591	2.997	0.102	0.118
D	2.692	3.099	0.106	0.122
e	0.838	1.041	0.033	0.041
H	0.080	0.254	0.003	0.010
L	0.300	0.610	0.012	0.024